



## P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY									
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)						
- 20	$0.025$ at $V_{GS} = -4.5 \text{ V}$	- 12 <sup>a</sup>							
	0.031 at V <sub>GS</sub> = - 2.5 V	- 12 <sup>a</sup>	24 nC						
	0.041 at V <sub>GS</sub> = - 1.8 V		24 110						
	0.070 at V <sub>GS</sub> = - 1.5 V	- 4							

### **FEATURES**

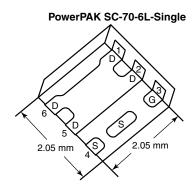
- TrenchFET® Power MOSFET New Thermally Enhanced PowerPAK® SC-70 Package
  - Small Footprint Area
  - Low On-Resistance
- 100 % R<sub>g</sub> Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

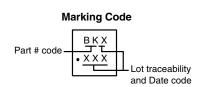
**HALOGEN** 

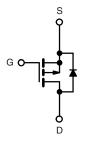
FREE

### **APPLICATIONS**

Load Switch, PA Switch and Battery Switch for Portable







### Ordering Information:

SiA431DJ-T4-GE3 (Lead (Pb)-free and Halogen-free) SiA431DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATING</b>	<b>S</b> T <sub>A</sub> = 25 °C, unles	ss otherwise note	ed			
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	- 20	V		
Gate-Source Voltage		V <sub>GS</sub>				
Continuous Drain Current (T <sub>J</sub> = 150 °C)	$T_{C} = 25 ^{\circ}\text{C}$ $T_{C} = 70 ^{\circ}\text{C}$ $T_{A} = 25 ^{\circ}\text{C}$ $T_{A} = 70 ^{\circ}\text{C}$	I <sub>D</sub>	- 12 <sup>a</sup> - 12 <sup>a</sup> - 9.6 <sup>b, c</sup> - 7.7 <sup>b, c</sup>	A		
Pulsed Drain Current	•	I <sub>DM</sub>	- 30			
Continuous Source-Drain Diode Current	$T_C = 25 ^{\circ}C$ $T_A = 25 ^{\circ}C$	I <sub>S</sub>	- 12 <sup>a</sup> - 2.9 <sup>b, c</sup>			
Maximum Power Dissipation	$T_{C} = 25  ^{\circ}C$ $T_{C} = 70  ^{\circ}C$ $T_{A} = 25  ^{\circ}C$ $T_{A} = 70  ^{\circ}C$	P <sub>D</sub>	19 12 3.5 <sup>b, c</sup> 2.2 <sup>b, c</sup>	w		
Operating Junction and Storage Temperature R	/\	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C		
Soldering Recommendations (Peak Temperatur	·e) <sup>d, e</sup>	J	260			

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 5 s	R <sub>thJA</sub>	28	36	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	5.3	6.5	7 0, 7				

### Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. See Solder Profile (<a href="https://www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under Steady State conditions is 80 °C/W.

Document Number: 65267 S12-1141-Rev. B, 21-May-12

For more information please contact: pmostechsupport@vishay.com

## SiA431DJ

## Vishay Siliconix



SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted									
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static									
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 20			V			
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = - 250 μA		- 14.5		mV/°C			
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	Ι <sub>D</sub> = - 250 μΑ		2.7					
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.4		- 0.85	V			
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA			
Zava Cata Valtaga Dvain Current	ı	V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V			- 1	μΑ			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			- 10				
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			Α			
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 6.5 A		0.020	0.025				
2		V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 5.8 A		0.025	0.031	Ω			
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 2.5 A		0.034	0.041				
		V <sub>GS</sub> = - 1.5 V, I <sub>D</sub> = - 1.5 A		0.045	0.070	1			
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 6.5 A		31		S			
Dynamic <sup>b</sup>					l.	l			
Input Capacitance	C <sub>iss</sub>			1700		pF			
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		230					
Reverse Transfer Capacitance	C <sub>rss</sub>			205					
Total Cata Charge	0	$V_{DS} = -10 \text{ V}, V_{GS} = -8 \text{ V}, I_{D} = -9.6 \text{ A}$		40	60	nC			
Total Gate Charge	Qg			24	36				
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -9.6 \text{ A}$		2.4					
Gate-Drain Charge	$Q_{gd}$			6.5					
Gate Resistance	$R_g$	f = 1 MHz	1.3	6.3	13	Ω			
Turn-On Delay Time	t <sub>d(on)</sub>			22	35				
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, R_{L} = 1.3 \Omega$		25	40				
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 7.7 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 $\Omega$		65	100				
Fall Time	t <sub>f</sub>			25	40				
Turn-On Delay Time	t <sub>d(on)</sub>			10	15	ns			
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, R_L = 1.3 \Omega$		10	15	1			
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong -7.7 \text{ A}, V_{GEN} = -8 \text{ V}, R_g = 1 \Omega$		65	100				
Fall Time	t <sub>f</sub>			20	30				
Drain-Source Body Diode Characterist	ics								
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 12	- A			
Pulse Diode Forward Current	I <sub>SM</sub>				- 30				
Body Diode Voltage	$V_{SD}$	I <sub>S</sub> = - 7.7 A, V <sub>GS</sub> = 0 V		- 0.8	- 1.2	V			
Body Diode Reverse Recovery Time	t <sub>rr</sub>			35	60	ns			
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = - 7.7 A, dl/dt = 100 A/μs, T <sub>J</sub> = 25 °C		21	35	nC			
Reverse Recovery Fall Time	t <sub>a</sub>	$\frac{1}{1} = -7.7 \text{ A}, \text{ dival} = 100 \text{ A/} \mu \text{s}, \text{ 1J} = 25 \text{ C}$		20		no			
Reverse Recovery Rise Time	t <sub>b</sub>			15		ns			

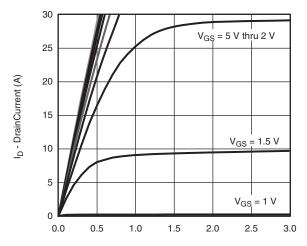
### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

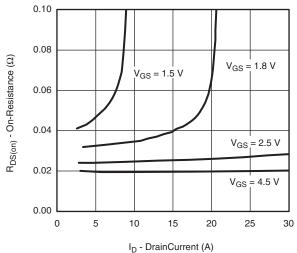


## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

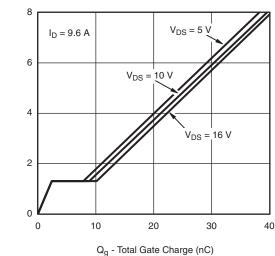


V<sub>DS</sub> - Drain-to-Source Voltage (V)

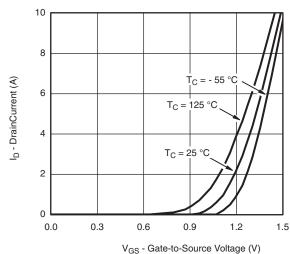
### **Output Characteristics**



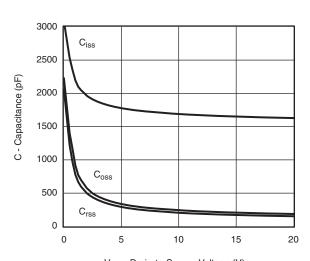
## On-Resistance vs. Drain Current and Gate Voltage



### **Gate Charge**

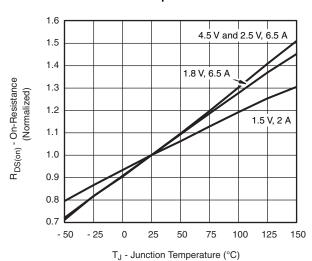


**Transfer Characteristics** 



V<sub>DS</sub> - Drain-to-Source Voltage (V)

### Capacitance



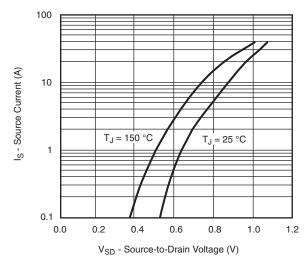
On-Resistance vs. Junction Temperature

V<sub>GS</sub> - Gate-to-Source Voltage (V)

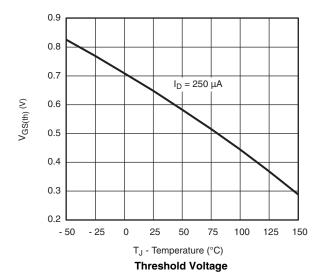
## SiA431DJ

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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

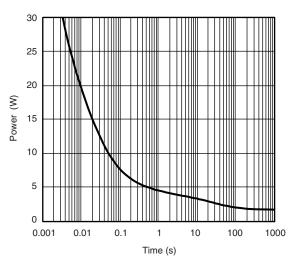


### Soure-Drain Diode Forward Voltage

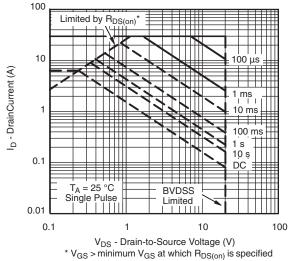


0.08 6.5 A, 25 °C I<sub>D</sub> = 2 A, 125 °C 0.06  $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$  - On-Resistance  $(\Omega)$  $I_D = 6.5 \text{ A}, 125 \,^{\circ}\text{C}$ 0.04 I<sub>D</sub> = 2 A, 25 °C 0.02 0.00 2 3 5 0 4

V<sub>GS</sub> - Gate-to-Source Voltage (V) On-Resistance vs. Gate-to-Source Voltage



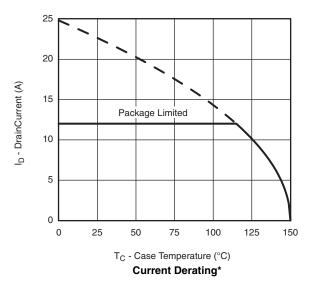
Single Pulse Power, Junction-to-Ambient

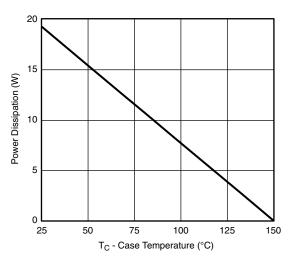


Safe Operating Area, Junction-to-Ambient



## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





**Power Derating** 

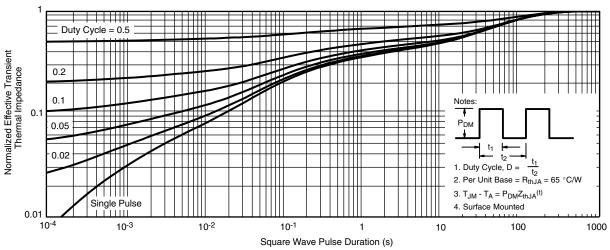
<sup>\*</sup> The power dissipation  $P_D$  is based on  $T_{J(max)}$  = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

## SiA431DJ

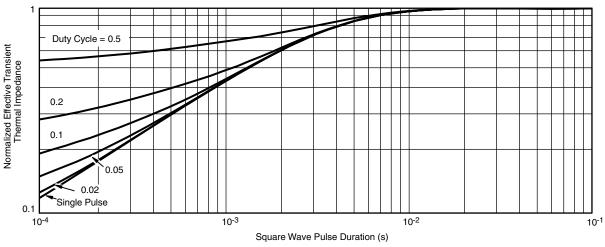
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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



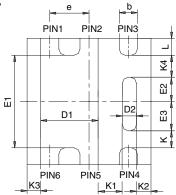
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65267.





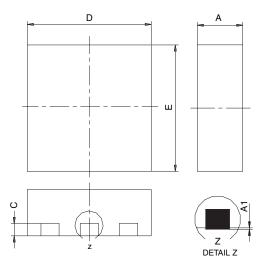
## PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
   Package outline exclusive of mold flash and metal burr
   Package outline inclusive of plating

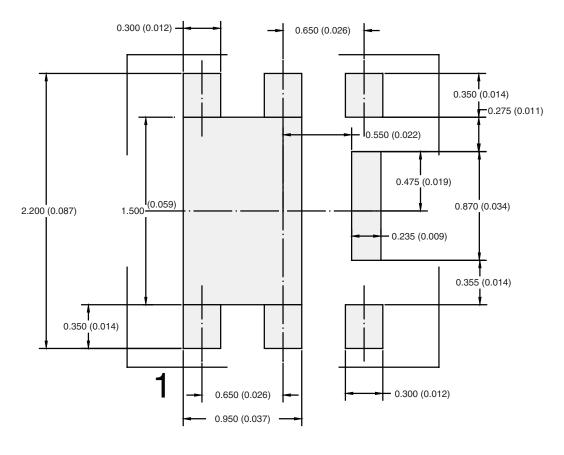
	SINGLE PAD						DUAL PAD						
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
<b>A</b> 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028	
D2	0.135	0.235	0.335	0.005	0.009	0.013							
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC			0.65 BSC			0.026 BSC		
K		0.275 TYP	١		0.011 TYP		0.275 TYP			0.011 TYP			
K1		0.400 TYP	١		0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP	1	0.009 TYP		0.252 TYP		0.010 TYP					
К3		0.225 TYP	1	0.009 TYP									
K4		0.355 TYP	<u> </u>		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
Т							0.05	0.10	0.15	0.002	0.004	0.006	
FCN: C-07431 – Bey C. 06-Aug-07													

DWG: 5934

Document Number: 73001 06-Aug-07



## RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

Return to Index

ATTLICATION NOT



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Revision: 13-Jun-16 1 Document Number: 91000

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